Short communication

Effect of temperature and soaking time on the synthesis of Mo(Al,Si)₂

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Abstract

Mo(Al,Si)₂ has been prepared by hot pressing elemental powders of Mo, Al and Si, at 1200–1700°C and 22 MPa. Mo₅Si₃ or Mo₅Si₃C have been observed as minor phases in all the samples with 1300°C being the best processing temperature for synthesizing Mo(AlSi)₂: with minimum amount of impurities. As the soaking time increases, the amount of impurity phases also increases. © 2001 Elsevier Science Ltd and Techna S.r.l. All rights reserved.

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1. Introduction

MoSi₂ is a good high temperature structural material for use in aggressive environments. This stems from its high melting point (2030°C), excellent high temperature oxidation and corrosion resistance and moderate density (6.31 g/cc). However, MoSi₂, has some disadvantages like brittleness at temperatures lower than 1000°C, and poor creep resistance at temperatures above 1250°C, and it undergoes pesting at intermediate temperatures (300–600°C) [1–3]. It has been reported that aluminium addition to MoSi₂ and thus formation of Mo(Al,Si)₂ could improve the mechanical and oxidation properties of MoSi₂ [1]. MoSi₂ has a Cllb-type body centered tetragonal structure at temperatures lower than 1900°C and a C40 type hexagonal structure at temperatures higher than 1900°C [4]. Mo(Al,Si)₂ has a C40 type hexagonal structure at all temperatures. Therefore, Mo(Al,Si)₂ can be considered to be a high temperature hexagonal modification of MoSi₂, stabilized by the partial substitution of aluminium for silicon. Indeed, the improved mechanical properties of Mo(Al,Si)₂ are attributed to its more symmetric C40 hexagonal structure. The pesting of MoSi₂ at lower temperatures is also suppressed by aluminium addition, the volume change in the oxidation of Mo(Al,Si)₂ being much smaller (+4.9 vol.%) than for

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MoSi₂ (+85.6 vol.%). Mo(Al,Si)₂ prepared by micropyretic synthesis has some improved properties viz. higher fracture toughness, higher oxidation resistance etc. [4]. Mo(Al,Si)₂ has been synthesised to a good density by several methods viz., SHS with Mo, Al and Si [5], reactive hot pressing of MoSi₂, Mo and Al powders [6] and arc melting [1,2]. However, all these materials contained secondary unwanted phases and impurities. This work accounts for the preparation of high purity Mo(Al,Si)₂ by the hot pressing of elemental powders. From reactive infiltration of aluminium into MoSi₂ it was found that 17 at.% of Al reacted with MoSi₂ irrespective of the temperature and duration of infiltration [7]. Hence, the percentage chosen for aluminium was 17 at.% which also corresponds to the most stable form of Mo(Al,Si)2 as evident from the phase diagram [8]. Hot pressing temperatures and soaking times were varied in an attempt to get Mo(Al,Si)₂ with the least amount of impurity phases.

2. Experimental procedure

Commercially available 99.5% pure Mo, Al and Si powders were mixed in stoichiometric proportion to obtain Mo_{33.3}A1₁₇Si_{49.6}. Pellets were prepared by hot pressing batches of 1.5 gm of the mixture at 22 MPa in argon atmosphere at 1050–1700°C. Synthesis was also carried out at a constant temperature of 1300°C and different sintering times. All the specimens were then

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carefully polished for X-ray (D/Max 2200 Ultima X-ray Diffractometer) and microstructure analysis (LEO 4401).

3. Results and discussion

X-ray diffraction patterns of samples synthesized at different temperatures show Mo(Al,Si)₂ as the major phase (Table 1). In addition, samples prepared at temperatures lower than 1300°C contained Mo₅Si₃, Mo and Si as impurities. Samples prepared at 1500°C contained Mo₅Si₃, Mo₅Si₃C and Si as impurities. Above 1500°C i.e. at 1600 and 1700°C samples contain only Mo₅Si₃ and Mo₅Si₃C as impurities. Thus, samples prepared between 1300 and 1400°C contain the lowest amount of impurities in the form of Mo₅Si₃ though Mo₅Si₃ peaks at 1400°C are more intense than at 1300°C. A scanning electron micrograph of Mo(Al,Si)₂ prepared at 1300°C is shown in Fig. 1. Mo(Al,Si)₂ appears as dark grey particles and the aluminium content as calculated from the EDX analysis of the grey particles is in the range of 12–18 at.%.

At lower temperatures (<1300°C, i.e. 1050–1200°C) reactions may be incomplete. Hence, along with Mo(Al,Si)₂ there remain some unreacted Mo, Al and Si. Aluminium may be present as Al₂O₃. On the other

Table 1

Phases present
Mo(Al,Si) ₂ , Mo ₅ Si ₃ , Mo,Si
Mo(Al,Si) ₂ , Mo ₅ Si ₃
Mo(Al,Si) ₂ , Mo ₅ Si ₃
Mo(Al,Si) ₂ , Mo ₅ Si ₃ , Mo ₅ Si ₃ C ₃ , Si
Mo(Al,Si) ₂ , Mo ₅ Si ₃ , Mo ₅ Si ₃ C
Mo(Al,Si) ₂ , Mo ₅ Si ₃ , Mo ₅ Si ₃ C

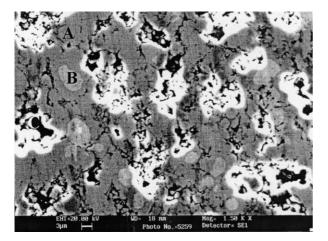


Fig. 1. Scanning electron micrograph of $Mo(Al,Si)_2$ prepared at $1300^{\circ}C$. $Mo(Al,Si)_2$ appears as dark grey particles (A), lighter coloured spots are due to Mo_5Si_3 (B) and the black regions correspond to the pores (C).

hand, at 1500°C Mo(Al,Si)₂ is unstable and starts decomposing as follows:

$$7\text{MoAl}_{0.5}\text{Si}_{1.5} \rightarrow \text{Mo}_5\text{Si}_3 + 3.5\text{Al} + 2\text{Mo} + 7.5\text{Si}$$
 (1)

At these temperatures the Mo_5Si_3 reacts with C (from the graphite die) to form Mo_5Si_3C . So at $1500^{\circ}C$ there are impurities like Mo_5Si_3 , Mo_5Si_3C and Si. With further increase in temperature i.e. at 1600 and $1700^{\circ}C$, there exists $Mo(Al,Si)_2$ along with some impurities of Mo_5Si_3 and Mo_5Si_3C . Thus, in all the samples prepared at different temperatures we can find that $Mo(Al,Si)_2$ is the major phase and Mo_5Si_3 is present as an impurity phase. The phase diagram of the Mo-Al-Si system [4] shows that $Mo(Al,Si)_2$ is stable only over a small compositional range. Hence, a little variation in composition leads to the formation of Mo_5Si_3 as an impurity phase.

Samples prepared at 1300°C proved to contain the lowest amount of Mo₅Si₃. Consequently, in another set of experiments Mo(Al,Si)₂ was prepared at a constant temperature of 1300°C and varying the hot pressing time. Fig. 2 shows the X-ray diffraction patterns of three samples prepared at 1300°C with soaking times of 15, 35 and 45 min. The X-ray diffraction peak corresponding to Mo₅Si₃ at 2θ of 42.65° starts becoming more intense with increasing soaking time, as given in Table 2. The less intense peaks (2θ: 62.0°, 67.7°, 70.1°, etc.) of Mo₅Si₃ start appearing as shoulders in the X-ray diffraction pattern of 35 min sintered sample giving an asymmetric look to the Mo(Al,Si)₂ peaks. In 45 min sintered sample these Mo₅Si₃ peaks increase in intensity and grow into

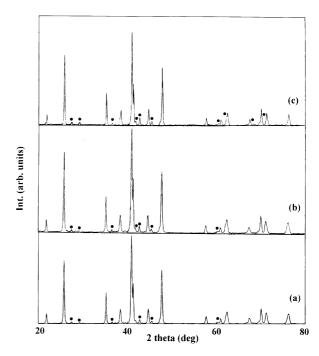


Fig. 2. X-ray diffraction pattern of Mo(Al,Si)₂ prepared at 1300° C with soaking time of (a) 15, (b) 35 and (c) 45 min; \bullet , Mo₅Si₃.

Table 2

Temperature (°C)	Soaking time (min)	I_1/I_2^{a}
1300	15	0.049
1300	35	0.063
1300	45	0.081

^a I₁, Intensity of Mo₅Si₃ peak; I₂, intensity of Mo(Al,Si)₂ peak.

clear peaks. It seems that $Mo(Al,Si)_2$ is not very stable at these temperatures for prolonged times. The concentration of Mo_5Si_3 increases because $Mo(Al,Si)_2$ which has already formed starts decomposing if it is kept at these temperatures for long periods of time.

4. Conclusions

Mo(Al,Si)₂ can be prepared with less than 10% impurity content by hot pressing elemental Mo,Si and

Al at a temperature of 1300°C for 15 min. Small variations in temperature or sintering time lead to an increase in impurities. The main impurity phase is Mo₅Si₃.

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